Congxin Xia

List of Publications by Year
in descending order

196 papers	5,254 citations	36 h-index (101496)	62 g-index (118793)
196 all docs	196 docs citations	196 times ranked	5319 citing authors

#	Article	IF	Citations
1	Highly Polarization-Sensitive, Broadband, Self-Powered Photodetector Based on Graphene/PdSe₂/Germanium Heterojunction. ACS Nano, 2019, 13, 9907-9917.	7.3	420
2	Universality of electronic characteristics and photocatalyst applications in the two-dimensional Janus transition metal dichalcogenides. Physical Review B, 2018, 98, .	1.1	229
3	Tunable Room-Temperature Ferromagnetism in Two-Dimensional Cr₂Te₃. Nano Letters, 2020, 20, 3130-3139.	4.5	175
4	A type-II GeSe/SnS heterobilayer with a suitable direct gap, superior optical absorption and broad spectrum for photovoltaic applications. Journal of Materials Chemistry A, 2017, 5, 13400-13410.	5.2	138
5	Enhanced rectification, transport property and photocurrent generation of multilayer ReSe2/MoS2 pâ€“n heterojunctions. Nano Research, 2016, 9, 507-516.	5.8	132
6	Interlayer coupling effects on Schottky barrier in the arsenene-graphene van der Waals heterostructures. Applied Physics Letters, 2015, 107, .	1.5	128
7	Various Structures of 2D Transitionâ€Metal Dichalcogenides and Their Applications. Small Methods, 2018, 2, 1800094.	4.6	107
8	Effects of strain and electric field on electronic structures and Schottky barrier in graphene and SnS hybrid heterostructures. Carbon, 2016, 109, 737-746.	5.4	106
9	Tuning the band gap of hematite Î±-Fe2O3 by sulfur doping. Physics Letters, Section A: General, Atomic and Solid State Physics, 2013, 377, 1943-1947.	0.9	98
10	The characteristics of n- and p-type dopants in SnS2monolayer nanosheets. Physical Chemistry Chemical Physics, 2014, 16, 19674.	1.3	98
11	Enhancement of hole mobility in InSe monolayer via an InSe and black phosphorus heterostructure. Nanoscale, 2017, 9, 14682-14689.	2.8	92
12	Elastic, electronic and optical properties of the two-dimensional PtX2 (Xâ€‰=â€‰S, Se, and Te) monolayer. Applied Surface Science, 2018, 435, 476-482.	3.1	89
13	The feasibility of tunable p-type Mg doping in a GaN monolayer nanosheet. Acta Materialia, 2013, 61, 7720-7725.	3.8	81
14	Composition-tunable 2D SnSe_{2(1âˆ’x)}S_{2x} alloys towards efficient bandgap engineering and high performance (opto)electronics. Journal of Materials Chemistry C, 2017, 5, 84-90.	2.7	81
15	Recent advances in optoelectronic properties and applications of two-dimensional metal chalcogenides. Journal of Semiconductors, 2016, 37, 051001.	2.0	75
16	Direct Wide Bandgap 2D GeSe₂ Monolayer toward Anisotropic UV Photodetection. Advanced Optical Materials, 2019, 7, 1900622.	3.6	70
17	Effects of Electric Field on the Electronic Structures of Broken-gap Phosphorene/ <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" overflow="scroll"><mml:mi>Sn</mml:mi><mml:msub><mml:mi>X</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>		

#	Article	IF	Citations
19	Type-II InSe/MoSe₂(WSe₂) van der Waals heterostructures: vertical strain and electric field effects. Journal of Materials Chemistry C, 2018, 6, 10010-10019.	2.7	59
20	Interlayer coupling and external electric field tunable electronic properties of a 2D type-I Î±-tellurene/MoS₂ heterostructure. Journal of Materials Chemistry C, 2018, 6, 10256-10262.	2.7	56
21	Tuning the electronic structures and magnetism of two-dimensional porous C₂N via transition metal embedding. Physical Chemistry Chemical Physics, 2016, 18, 22678-22686.	1.3	54
22	Electronic and magnetic properties of n-type and p-doped MoS₂ monolayers. RSC Advances, 2016, 6, 16772-16778.	1.7	54
23	Two-dimensional transition-metal dichalcogenides-based ferromagnetic van der Waals heterostructures. Nanoscale, 2017, 9, 17585-17592.	2.8	53
24	A theoretical simulation of small-molecules sensing on an S-vacancy SnS₂ monolayer. Physical Chemistry Chemical Physics, 2017, 19, 10470-10480.	1.3	52
25	n- and p-type dopants in the InSe monolayer via substitutional doping. Journal of Materials Science, 2017, 52, 7207-7214.	1.7	48
26	Tunable electronic structures and magnetism in arsenene nanosheets via transition metal doping. Journal of Materials Science, 2016, 51, 9504-9513.	1.7	46
27	Electronic and magnetic properties of X-doped (XÂ=ÂTi, Zr, Hf) tungsten disulphide monolayer. Journal of Alloys and Compounds, 2016, 654, 574-579.	2.8	45
28	Characteristics of p-type Mg-doped GaS and GaSe nanosheets. Physical Chemistry Chemical Physics, 2014, 16, 18799.	1.3	44
29	Band engineering of the MoS₂/stanene heterostructure: strain and electrostatic gating. Nanotechnology, 2017, 28, 195702.	1.3	44
30	Tunable donor and acceptor impurity states in a WSe₂ monolayer by adsorption of common gas molecules. RSC Advances, 2016, 6, 82793-82800.	1.7	43
31	Spinâ€"orbit coupling effects on electronic structures in stanene nanoribbons. Physical Chemistry Chemical Physics, 2016, 18, 6534-6540.	1.3	42
32	Electronic and magnetic properties of SnSe monolayers doped by Ga, In, As, and Sb: a first-principles study. Physical Chemistry Chemical Physics, 2016, 18, 8158-8164.	1.3	42
33	Effect of structural defects on electronic and magnetic properties of pristine and Mn-doped MoS2 monolayer. Solid State Communications, 2015, 220, 31-35.	0.9	41
34	Typeâ€I Transition Metal Dichalcogenides Lateral Homojunctions: Layer Thickness and External Electric Field Effects. Small, 2018, 14, e1800365.	5.2	41
35	Crossâ€Substitution Promoted Ultrawide Bandgap up to 4.5ÂeV in a 2D Semiconductor: Gallium Thiophosphate. Advanced Materials, 2021, 33, e2008761.	11.1	41
36	Electrostatic gating dependent multiple-band alignments in a high-temperature ferromagnetic Mg(OH) <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub><mml:mo>/</mml:mo><mml:msub><mml:mi>VS</mml:mi><mml:mn>2</mml:mn></mml:msub> heterobilayer. Physical Review B, 2017, 95, .	1.1	39

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37	Tuning anisotropic electronic transport properties of phosphorene via substitutional doping. Physical Chemistry Chemical Physics, 2016, 18, 25869-25878.	1.3	38
38	Modulation of electronic transport properties in armchair phosphorene nanoribbons by doping and edge passivation. Scientific Reports, 2017, 7, 12799.	1.6	38
39	Reversible Half Wave Rectifier Based on 2D InSe/GeSe Heterostructure with Nearâ€Broken Band Alignment. Advanced Science, 2021, 8, 1903252.	5.6	38
40	Photovoltaic Field-Effect Photodiodes Based on Double van der Waals Heterojunctions. ACS Nano, 2021, 15, 14295-14304.	7.3	37
41	The rectifying and negative differential resistance effects in graphene/h-BN nanoribbon heterojunctions. Physical Chemistry Chemical Physics, 2016, 18, 27976-27980.	1.3	36
42	Electronic and magnetic properties of 1T-HfS2 by doping transition-metal atoms. Applied Surface Science, 2016, 383, 151-158.	3.1	36
43	First-principles studies on substitutional doping by group IV and VI atoms in the two-dimensional arsenene. Applied Surface Science, 2016, 378, 350-356.	3.1	36
44	Effects of applied strain and electric field on small-molecule sensing by stanene monolayers. Journal of Materials Science, 2017, 52, 5083-5096.	1.7	36
45	Electronic characteristics of p-type transparent SnO monolayer with high carrier mobility. Applied Surface Science, 2017, 401, 114-119.	3.1	36
46	Electronic transport properties of the first all-boron fullerene B₄₀and its metallofullerene Sr@B₄₀. Physical Chemistry Chemical Physics, 2016, 18, 12024-12028.	1.3	35
47	Spin-dependent Dirac electrons and valley polarization in the ferromagnetic stanene/ <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Cr</mml:mi><mml:msub><mml:mi mathvariant="normal">I</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math> van der Waals heterostructure. Physical Review B, 2019, 100, .	1.1	35
48	Strain and Spinâ€“Orbital Coupling Effects on Electronic Structures and Magnetism of Semi-Hydrogenated Stanene. Journal of Physical Chemistry C, 2016, 120, 10622-10628.	1.5	34
49	Tunable electronic structures of <i>p</i>-type Mg doping in AlN nanosheet. Journal of Applied Physics, 2014, 116, .	1.1	33
50	Effective p-type N-doped WS2 monolayer. Journal of Alloys and Compounds, 2015, 649, 357-361.	2.8	33
51	Structural defects in pristine and Mn-doped monolayer WS2: A first-principles study. Superlattices and Microstructures, 2015, 85, 339-347.	1.4	32
52	Magnetic vanadium sulfide monolayers: transition from a semiconductor to a half metal by doping. Journal of Materials Chemistry C, 2016, 4, 8111-8120.	2.7	32
53	Gate-tunable diode-like current rectification and ambipolar transport in multilayer van der Waals ReSe₂/WS₂ pâ€“n heterojunctions. Physical Chemistry Chemical Physics, 2016, 18, 27750-27753.	1.3	30
54	Sn1âˆ’xTixS2 ternary alloys: A new visible optical material. Acta Materialia, 2014, 72, 223-228.	3.8	29

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55	Magnetic properties of two nearest Cu-doped monolayer WS 2 : A first-principles study. Solid State Communications, 2015, 217, 66-69.	0.9	29
56	Tuning electronic structures of the stanene monolayer via defects and transition-metal-embedding: spinâ€“orbit coupling. Physical Chemistry Chemical Physics, 2016, 18, 28759-28766.	1.3	29
57	Hydrogenic impurity states in zinc-blende InGaN quantum dot. Physica B: Condensed Matter, 2008, 403, 165-169.	1.3	28
58	Electronic and magnetic properties of X-doped (X=Ni, Pd, Pt) WS2 monolayer. Journal of Magnetism and Magnetic Materials, 2016, 414, 45-48.	1.0	28
59	Characteristics of n- and p-type dopants in 1T-HfS2 monolayer. Journal of Alloys and Compounds, 2016, 689, 302-306.	2.8	28
60	Magnetic doping in two-dimensional transition-metal dichalcogenide zirconium diselenide. Journal of Alloys and Compounds, 2017, 698, 611-616.	2.8	28
61	Out of plane stacking of InSe-based heterostructures towards high performance electronic and optoelectronic devices using a graphene electrode. Journal of Materials Chemistry C, 2018, 6, 12509-12517.	2.7	28
62	Asymmetric Ferroelectric-Gated Two-Dimensional Transistor Integrating Self-Rectifying Photoelectric Memory and Artificial Synapse. ACS Nano, 2022, 16, 11218-11226.	7.3	27
63	Band structure engineering of SnS₂/polyphenylene van der Waals heterostructure <i>via</i> interlayer distance and electric field. Physical Chemistry Chemical Physics, 2019, 21, 1521-1527.	1.3	26
64	Large scale fabrication of well-aligned CdS/p-Si shell/core nanowire arrays for photodetectors using solution methods. Physical Chemistry Chemical Physics, 2015, 17, 16784-16790.	1.3	25
65	Type-I Ca(OH)₂/Î±-MoTe₂ vdW heterostructure for ultraviolet optoelectronic device applications: electric field effects. Journal of Materials Chemistry C, 2017, 5, 12629-12634.	2.7	25
66	Modulation of the band structures and optical properties of holey C₂N nanosheets by alloying with group IV and V elements. Journal of Materials Chemistry C, 2016, 4, 9294-9302.	2.7	24
67	Light adatoms influences on electronic structures of the two-dimensional arsenene nanosheets. Solid State Communications, 2016, 230, 6-10.	0.9	24
68	Microwave-Assisted Hydrothermal Synthesis of CuS Nanoplate Films on Conductive Substrates as Efficient Counter Electrodes for Liquid-Junction Quantum Dot-Sensitized Solar Cells. Journal of the Electrochemical Society, 2017, 164, H215-H224.	1.3	24
69	Anti-ambipolar behavior and photovoltaic effect in p-MoTe₂/n-InSe heterojunctions. Journal of Materials Chemistry C, 2021, 9, 10372-10380.	2.7	24
70	Hydrostatic pressure effects on impurity states in InAs/GaAs quantum dot. Applied Surface Science, 2008, 254, 3479-3483.	3.1	23
71	High on/off ratio photosensitive field effect transistors based on few layer SnS₂. Nanotechnology, 2016, 27, 34LT01.	1.3	23
72	Two-dimensional Janus-In2STe/InSe heterostructure with direct gap and staggered band alignment. Applied Surface Science, 2020, 509, 145317.	3.1	23

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73	Spin-dependent electronic transport properties of zigzag silicon carbon nanoribbon. RSC Advances, 2015, 5, 107136-107141.	1.7	22
74	PtSe₂/graphene hetero-multilayer: gate-tunable Schottky barrier height and contact type. Nanotechnology, 2018, 29, 465707.	1.3	22
75	Electric field-tunable electronic structures of 2D alkaline-earth metal hydroxideâ€“graphene heterostructures. Journal of Materials Chemistry C, 2017, 5, 7230-7235.	2.7	21
76	Growth and Raman Scattering Investigation of a New 2D MOX Material: YbOCl. Advanced Functional Materials, 2019, 29, 1903017.	7.8	21
77	Strainâ€Induced Bandâ€Gap Tuning of 2Dâ€SnSSe Flakes for Application in Flexible Sensors. Advanced Materials Technologies, 2020, 5, 1900853.	3.0	21
78	First-principles study of group V and VII impurities in SnS2. Superlattices and Microstructures, 2015, 85, 664-671.	1.4	20
79	Perseverance of direct bandgap in multilayer 2D PbI ₂ under an experimental strain up to 7.69%. 2D Materials, 2019, 6, 025014.	2.0	20
80	External electric field and strains facilitated nitrogen dioxide gas sensing properties on 2D monolayer and bilayer SnS2 nanosheets. Applied Surface Science, 2019, 491, 128-137.	3.1	20
81	Controllable preparation of ultrathin 2D BiOBr crystals for high-performance ultraviolet photodetector. Science China Materials, 2021, 64, 189-197.	3.5	20
82	Electronic and magnetic properties of Ag-doped monolayer WS2 by stain. Journal of Alloys and Compounds, 2016, 680, 659-664.	2.8	19
83	Effect of strain on electronic and magnetic properties of Fe-doped monolayer SnS 2. Physics Letters, Section A: General, Atomic and Solid State Physics, 2017, 381, 1732-1737.	0.9	19
84	Enhanced Carrier Concentration and Electronic Transport by Inserting Graphene into van der Waals Heterostructures of Transition-Metal Dichalcogenides. Physical Review Applied, 2018, 10, .	1.5	19
85	Spin orientation and strain tuning valley polarization with magneto-optic Kerr effects in ferrovalley VS2 monolayer. Applied Physics Letters, 2020, 117, .	1.5	19
86	Hydrogenic impurity in zinc-blende GaN/AlGaN quantum dot. Microelectronics Journal, 2007, 38, 663-666.	1.1	18
87	Hydrostatic pressure effects on exciton states in InAs/GaAs quantum dots. Superlattices and Microstructures, 2008, 43, 285-291.	1.4	18
88	Tunable electronic structures in the two-dimension SnX 2 (X = S and Se) nanosheets by stacking effects. Applied Surface Science, 2015, 356, 1200-1206.	3.1	17
89	Influences of the adsorption of different elements on the electronic structures of a tin sulfide monolayer. Physical Chemistry Chemical Physics, 2017, 19, 5423-5429.	1.3	17
90	Interface-controlled band alignment transition and optical properties of Janus MoSSe/GaN vdW heterobilayers. Journal Physics D: Applied Physics, 2020, 53, 055104.	1.3	17

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91	Silicene/BN vdW heterostructure as an ultrafast ion diffusion anode material for Na-ion battery. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 122, 114146.	1.3	17
92	Efficiency Enhancement Mechanism for Poly(3,) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 707 Td (4-ethylenedioxythiophene):Poly(styrenesu Treatment. Nanoscale Research Letters, 2016, 11, 267.	3.1	16
93	2D GeSe/SnS2(SnSe2) broken-gap heterostructures for tunnel field-effect transistors applications. Journal Physics D: Applied Physics, 2019, 52, 455103.	1.3	16
94	Using ferroelectric polarization to regulate and preserve the valley polarization in a <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>HfN</mml:mi><mml:mn>2</mml:mn></mm heterotrilayer. Physical Review B, 2021, 103, .	1.1	16
95	3d transition metal doping-induced electronic structures and magnetism in 1T-HfSe₂ monolayers. RSC Advances, 2017, 7, 52747-52754.	1.7	15
96	Rectification effects of C3N nanoribbons-based Schottky junctions. Carbon, 2019, 141, 363-369.	5.4	15
97	Few-layer In_{4/3}P₂Se₆ nanoflakes for high detectivity photodetectors. Nanoscale, 2021, 13, 3757-3766.	2.8	15
98	In-plane ferroelectricity in few-layered GeS and its van der Waals ferroelectric diodes. Nanoscale, 2021, 13, 16122-16130.	2.8	15
99	Hydrogenic impurity states in zinc-blende GaN/AlN coupled quantum dots. Physics Letters, Section A: General, Atomic and Solid State Physics, 2008, 372, 6420-6423.	0.9	14
100	Electric field effect on the donor impurity states in zinc-blende symmetric InGaN/GaN coupled quantum dots. Physics Letters, Section A: General, Atomic and Solid State Physics, 2009, 374, 97-100.	0.9	14
101	Electron and impurity states in GaN/AlGaN coupled quantum dots: Effects of electric field and hydrostatic pressure. Journal of Applied Physics, 2010, 108, 054307.	1.1	14
102	Magnetism induced by 3d transition metal atom doping in InSe monolayer. Journal of Materials Science, 2018, 53, 3500-3508.	1.7	14
103	Exciton states and oscillator strength in few-layer Î±-tellurene. Applied Physics Letters, 2019, 114, .	1.5	14
104	Self-driven SnS_{1â^’<i>x</i>}Se_{<i>x</i>} alloy/GaAs heterostructure based unique polarization sensitive photodetectors. Nanoscale, 2021, 13, 15193-15204.	2.8	14
105	Exciton states in zinc-blende GaN/AlGaN quantum dot: Effects of electric field and hydrostatic pressure. Physica B: Condensed Matter, 2010, 405, 2706-2710.	1.3	13
106	Band alignment tuning in GeS/arsenene staggered heterostructures. Journal of Alloys and Compounds, 2019, 793, 283-288.	2.8	13
107	Barrier width dependence of the donor binding energy of hydrogenic impurity in wurtzite InGaN/GaN quantum dot. Journal of Applied Physics, 2009, 106, 094301.	1.1	12
108	Electric field modulations of band alignments in arsenene/Ca(OH)₂heterobilayers for multi-functional device applications. Journal Physics D: Applied Physics, 2017, 50, 415304.	1.3	12

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109	Modulation of the electronic properties and spin polarization of 2H VS₂ nanoribbons by tuning ribbon widths and edge decoration. Physical Chemistry Chemical Physics, 2019, 21, 18211-18218.	1.3	12
110	Franzâ€“Keldysh effect in the interband optical absorption of semiconducting nanostructures. Journal of Applied Physics, 2009, 105, 084313.	1.1	11
111	Donor impurity states in zinc-blende InGaN/GaN asymmetric coupled quantum dots: Hydrostatic pressure effect. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2041-2046.	1.3	11
112	Effects of applied electric field and hydrostatic pressure on donor impurity states in cylindrical GaN/AlN quantum dot. Journal of Applied Physics, 2010, 107, 014305.	1.1	11
113	Strain effect on the electronic properties of Ce-doped SnS2 monolayer. Physica B: Condensed Matter, 2018, 547, 1-5.	1.3	11
114	Realization of larger band gap opening of graphene and type-I band alignment with BN intercalation layer in graphene/ <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>M</mml:mi><mml:msub><mml:mi>X</mml:mi><mml:mn heterojunctions. Physical Review B, 2019, 100, .	1.1	11
115	Strain effect of high Tc ferromagnetism in Mo-doped SnS2 monolayer. Computational Materials Science, 2019, 156, 321-324.	1.4	11
116	Silicene/boron nitride heterostructure for the design of highly efficient anode materials in lithium-ion battery. Journal of Physics Condensed Matter, 2020, 32, 355502.	0.7	11
117	Electronic and magnetic properties of Mn-doped monolayer WS2. Solid State Communications, 2015, 215-216, 1-4.	0.9	10
118	Strain-dependent electronic and magnetic properties of Au-doped WS2 monolayer. Solid State Communications, 2016, 230, 35-39.	0.9	10
119	VS₂ nanosheet as a promising candidate of recycle and reuse NO₂ gas sensor and capturer: a DFT study. Journal of Physics Condensed Matter, 2021, 33, 165501.	0.7	10
120	Built-in electric field effect on the hydrogenic donor impurity in wurtzite InGaN quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2714-2719.	1.3	9
121	Excitonic optical absorption in wurtzite InGaN/GaN quantum wells. Superlattices and Microstructures, 2012, 51, 9-15.	1.4	9
122	Finite barrier width effects on exciton states and optical properties in wurtzite InGaN/GaN quantum well. Journal of Luminescence, 2012, 132, 607-611.	1.5	9
123	Electronic structures and optical properties of SnSe2(1â^'x)O2x alloys. Computational Materials Science, 2014, 95, 712-717.	1.4	9
124	Carbon-doping-induced negative differential resistance in armchair phosphorene nanoribbons. Journal of Semiconductors, 2017, 38, 033005.	2.0	9
125	First-principles study of monolayer SnS2(1â^'x)Se2x alloys as anode materials for lithium ion batteries. Applied Surface Science, 2018, 457, 256-263.	3.1	9
126	Donor impurity states in wurtzite InGaN staggered quantum wells. Applied Physics Letters, 2011, 99, 203110.	1.5	8

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127	Laser field and electric field effects on exciton states and optical properties in zinc-blende GaN/AlGaN quantum well. Journal of Applied Physics, 2013, 113, .	1.1	8
128	Band gap scaling laws in group IV nanotubes. Nanotechnology, 2017, 28, 115202.	1.3	8
129	Substrate-induced phase control of In2Se3 thin films. Journal of Alloys and Compounds, 2020, 845, 156270.	2.8	8
130	Electronic properties of XPtY-Graphene (X/Y = S, Se and Te) contacts. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 124, 114311.	1.3	8
131	Low-temperature deposition of 2D SnS nanoflakes on PET substrates for flexible photodetectors with broadband response. Semiconductor Science and Technology, 2020, 35, 115016.	1.0	8
132	Shallow-donor impurity in zinc-blende InGaN/GaN asymmetric coupled quantum dots: Effect of electric field. Journal of Applied Physics, 2010, 107, 054305.	1.1	7
133	Effects of laser field and electric field on impurity states in zinc-blende GaN/AlGaN quantum well. Physics Letters, Section A: General, Atomic and Solid State Physics, 2011, 375, 2652-2655.	0.9	7
134	Electric field effects on optical properties in zinc-blende InGaN/GaN quantum dot. Journal of Luminescence, 2011, 131, 623-627.	1.5	7
135	Tunable built-in electric field and optical properties in wurtzite ZnO/MgZnO quantum wells. Physics Letters, Section A: General, Atomic and Solid State Physics, 2014, 378, 2251-2255.	0.9	7
136	First-principles study of sulfur atom doping and adsorption on Î±â€"Fe2O3 (0001) film. Physics Letters, Section A: General, Atomic and Solid State Physics, 2016, 380, 3149-3154.	0.9	7
137	Robust electronic and mechanical properties to layer number in 2D wide-gap X(OH)₂ (Xâ€‰â€‰=â€‰â€‰Mg, Ca). Journal Physics D: Applied Physics, 2018, 51, 015107.	1.3	7
138	Two-dimensional ferromagnetic materials and related van der Waals heterostructures: a first-principle study. Journal of Semiconductors, 2019, 40, 081509.	2.0	7
139	A ternary SnS1.26Se0.76 alloy for flexible broadband photodetectors. RSC Advances, 2019, 9, 14352-14359.	1.7	7
140	Hydrogenic donor states in wurtzite InGaN/GaN coupled quantum dots. Physics Letters, Section A: General, Atomic and Solid State Physics, 2007, 372, 64-67.	0.9	6
141	Exciton states in zinc-blende InGaN/GaN quantum dot. Current Applied Physics, 2008, 8, 153-158.	1.1	6
142	Shallow-donor impurity in vertical-stacked InGaN/GaN multiple-quantum wells: Electric field effect. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 43, 458-461.	1.3	6
143	Hydrogenic impurity states in zinc-blende InGaN/GaN asymmetric coupled quantum dots. Superlattices and Microstructures, 2010, 47, 624-630.	1.4	6
144	Barrier width and built-in electric field effects on hydrogenic impurity in wurtzite GaN/AlGaN quantum well. Physica E: Low-Dimensional Systems and Nanostructures, 2011, 44, 511-514.	1.3	6

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145	Tailoring the electronic structure of Mn-doped SnTe via strain. Journal of Materials Science, 2018, 53, 15995-16000.	1.7	6
146	Strain-tunable p-type Ag doping in the native n-type InSe monolayer. Applied Surface Science, 2018, 462, 387-392.	3.1	6
147	Evenâ€“odd oscillation of bandgaps in GeP₃ nanoribbons and a tunable 1D lateral homogenous heterojunction. Physical Chemistry Chemical Physics, 2019, 21, 275-280.	1.3	6
148	Tuning the magnetic anisotropy of ferromagnetic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>MnS</mml:mi><mml:mn>2</mml:mn></mml:msub></mn monolayers via electron occupation of Mn <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>d</mml:mi></mml:math> orbitals. Physical Review B, 2021, 104, .	1.1	6
149	The donor bound exciton states in wurtzite GaN quantum dot. Current Applied Physics, 2009, 9, 39-43.	1.1	5
150	Tuning electronic structure of SnS2 nanosheets by vertical electric field: a first-principles investigation. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	1.1	5
151	Impurity states in InSe monolayers doped with group II and IV elements. Journal of Applied Physics, 2017, 122, 185702.	1.1	5
152	Strain effect on SnS2 nanoribbons: Robust direct bandgap of zigzag-edge and sensitive indirect semiconductor with armchair-edge states. Superlattices and Microstructures, 2017, 111, 480-486.	1.4	5
153	Quantum size and electric field modulations on electronic structures of SnS₂/BN hetero-multilayers. Journal Physics D: Applied Physics, 2018, 51, 215303.	1.3	5
154	Quantum Confinement Effects on Excitonic Properties in the 2D vdW quantum system: The ZnO/WSe₂ Case. Advanced Photonics Research, 2021, 2, 2000114.	1.7	5
155	Magnetoelectric coupling effects on the band alignments of multiferroic In₂Se₃â€“CrI₃ trilayer heterostructures. Nanoscale, 2022, 14, 5454-5461.	2.8	5
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